- Member of the Texas Instruments Widebus™ Family
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 16-bit buffer/driver is designed for 1.65-V to $3.6\text{-V}\ \text{V}_{\text{CC}}$ operation.

The SN74ALVC16244A is designed specifically to improve the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable (OE) inputs.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE (each 4-bit buffer)

INP	JTS	OUTPUT
OE	Α	Υ
L	Н	Н
L	L	L
Н	Χ	Z

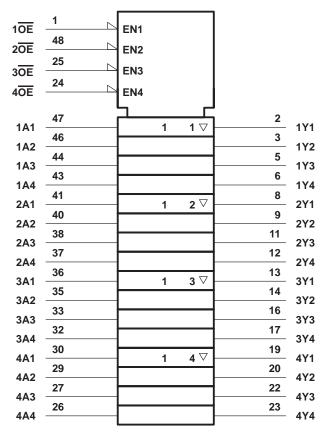
DGG OR DL PACKAGE (TOP VIEW)

	- 1			_	1	
1 <mark>OE</mark>	þ	1	U	48	þ	2 <mark>OE</mark>
1Y1	q	2		47	0	1A1
1Y2		3		46	0	1A2
GND		4		45	1	GND
1Y3		5		44		1A3
1Y4		6		43		1A4
V_{CC}		7		42		V_{CC}
2Y1		8		41		2A1
2Y2		9		40	•	2A2
GND		10		39	•	GND
2Y3		11		38	•	2A3
2Y4		12		37	1	2A4
3Y1		13		36		3A1
3Y2		14		35		3A2
GND		15		34	1	GND
3Y3		16		33	•	3A3
3Y4		17		32	•	3A4
V_{CC}		18		31	1	V_{CC}
4Y1		19		30	1	4A1
4Y2		20		29		4A2
GND		21		28	•	GND
4Y3		22		27	•	4A3
4Y4		23		26		4A4
40E	9	24		25		3 <mark>OE</mark>

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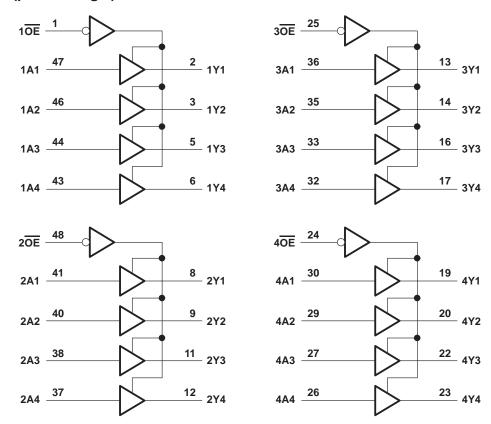
logic symbol†



 $[\]ensuremath{^{\dagger}}$ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, V _O (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, $I_{ K }(V_{ } < 0)$	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	89°C/W
DL package	94°C/W
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



SN74ALVC16244A **16-BIT BUFFER/DRIVER** WITH 3-STATE OUTPUTS SCAS250G – JANUARY 1993 – REVISED FEBRUARY 1999

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
VCC	Supply voltage		1.65	3.6	V
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}		
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	
٧ı	Input voltage		0	VCC	V
٧o	Output voltage		0	VCC	V
		V _{CC} = 1.65 V		-4	
la	High-level output current $ V_{CC} = 2.3 \text{ V} $ $ V_{CC} = 2.7 \text{ V} $	V _{CC} = 2.3 V		-12	mA
ЮН		V _{CC} = 2.7 V		-12	
		VCC = 3 V		-24	
		V _{CC} = 1.65 V		4	
	Lave lavel autout aussaut	V _{CC} = 2.3 V		12	mA
IOL	I OW-IEVELOUIDUIT CUITENT	V _{CC} = 2.7 V		12	
	V _{CC} = 3 V			24	
Δt/Δν	Input transition rise or fall rate	-		10	ns/V
T _A	Operating free-air temperature		-40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

P/	ARAMETER	TEST CO	VCC	MIN	TYP [†]	MAX	UNIT		
		I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	2			
		I _{OH} = -4 mA	$I_{OH} = -4 \text{ mA}$						
		I _{OH} = -6 mA	2.3 V	2					
Voн				2.3 V	1.7			V	
		I _{OH} = -12 mA		2.7 V	2.2				
			3 V	2.4					
		I _{OH} = -24 mA		3 V	2				
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2		
		I _{OL} = 4 mA	1.65 V			0.45	٧		
\ _{\/a} .		I _{OL} = 6 mA	2.3 V			0.4			
VOL		le. – 12 mA		2.3 V					0.7
		I _{OL} = 12 mA	2.7 V			0.4			
		I _{OL} = 24 mA		3 V			0.55		
Ц		$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ	
loz		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ	
Icc		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ	
∆lcc		One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ	
Control inputs		V. Van er CND		221/	3			n.E	
Ci	Data inputs	VI = VCC or GND		3.3 V	6			pF	
Co	Outputs	$V_O = V_{CC}$ or GND		3.3 V		7		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V	V _{CC} =	2.5 V 2 V	V _{CC} =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
	(INFO1)	(001F01)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	А	Υ	‡	1	3.7		3.6	1	3	ns
t _{en}	ŌĒ	Υ	‡	1	5.7		5.4	1	4.4	ns
^t dis	ŌĒ	Υ	‡	1	5.2		4.6	1	4.1	ns

[‡] This information was not available at the time of publication.

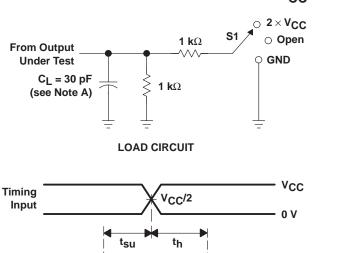
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS V _{CC} = 1.8 V V _{CC} = 2.5 V V _{CC}		V _{CC} = 3.3 V	UNIT		
	FARAMETER		1E31 CONDITIONS	TYP	TYP	TYP	ONIT
	Power dissipation	Outputs enabled	C ₁ = 50 pF. f = 10 MHz	‡	16	19	pF
C _{pd}	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	‡	4	5	рг

[‡] This information was not available at the time of publication.



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V}$

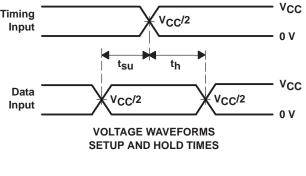


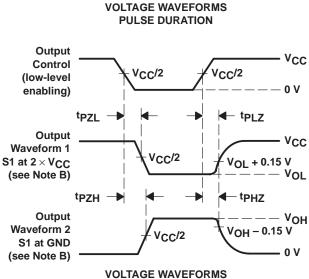


VCC

0 V

V_{CC}/2

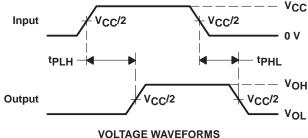




ENABLE AND DISABLE TIMES

V_{CC}/2

Input



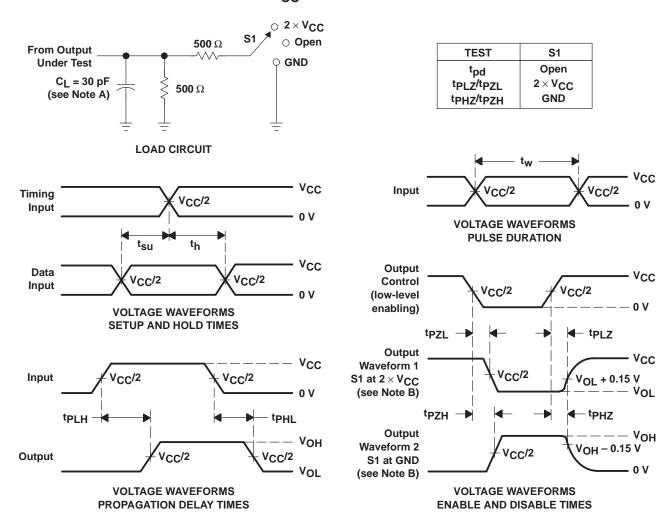
PROPAGATION DELAY TIMES

- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

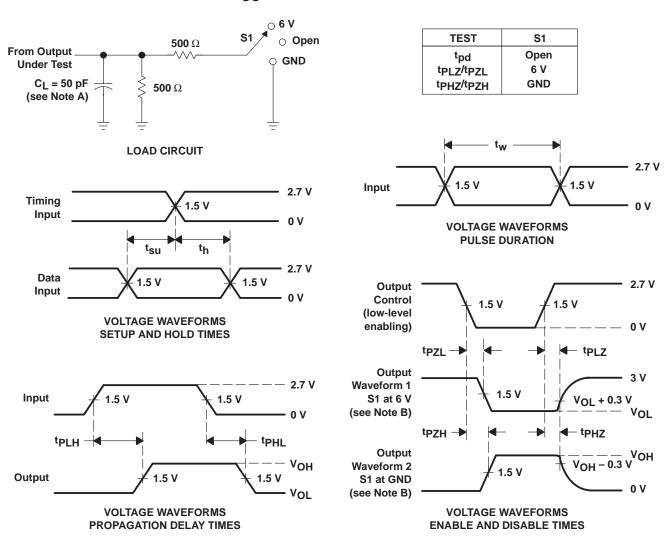


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2.5$ ns. $t_f \leq 2.5$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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